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Docket No.: 61352-075

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of : Customer Number: 20277  
: :  
Nobuyuki OTSUKA, et al. : Confirmation Number: 2226  
: :  
Application No.: 10/817,035 : Group Art Unit: 2811  
: :  
Filed: April 05, 2004 : Examiner:  
: :  
For: A GALLIUM INDIUM NITRIDE ARSENIDE BASED EPITAXIAL WAFER, A  
HETERO FIELD EFFECT TRANSISTOR USING THE WAFER, AND A METHOD OF  
FABRICATING THE HETERO FIELD EFFECT TRANSISTOR

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

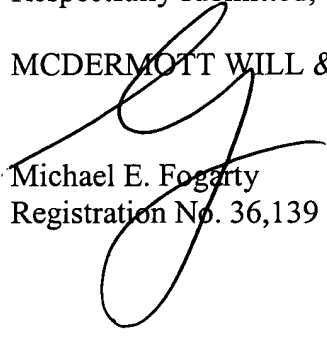
This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

10/817,035

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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**Date: September 23, 2004**

INFORMATION DISCLOSURE CITATION IN AN APPLICATION						ATTY. DOCKET NO. <b>61352-075</b>		SERIAL NO. <b>10/817,035</b>			
(PTO-1449)						APPLICANT <b>Nobuyuki OTSUKA, et al.</b>					
						FILING DATE <b>April 05, 2004</b>		GROUP <b>2811</b>			
U.S. PATENT DOCUMENTS											
EXAMINER'S INITIALS		CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)		Publication Date MM-DD-YYYY		Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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FOREIGN PATENT DOCUMENTS											
EXAMINER'S INITIALS		CITE NO.	Foreign Patent Document Country Codes - Number 4 - Kind Codes (if known)		Publication Date MM-DD-YYYY		Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines Where Relevant Figures Appear	Translation	
										Yes	No
				JP 2003-289082 A		10/10/2003	MATSUSHITA ELECTRIC IND CO LTD			JAPAN (w/English Abstract)	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)											
EXAMINER'S INITIALS		CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.								
EXAMINER						DATE CONSIDERED					